

N-Channel Enhancement Mode Power MOSFET

Description

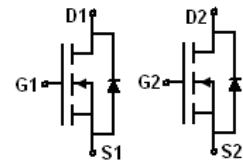
The HM30D0808 Duses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch and PWM applications.

General Features

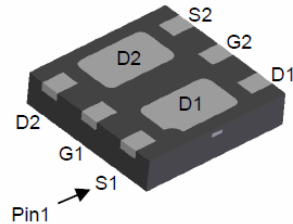
- $V_{DS} = 30V, I_D = 8.0A$
 $R_{DS(ON)} < 25m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 35m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- General Purpose Interfacing Switch
- Power Management Functions



Schematic diagram



DFNWB2X2-6L Bottom View

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM30D0808D	HM30D0808D	DFNWB2X2-6L	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	8	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	24	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
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Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.5	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A	-	22	25	mΩ
		V _{GS} =4.5V, I _D =5A	-	28	34	mΩ
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	558	-	PF
Output Capacitance	C _{OSS}		-	72.7	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	62.6	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =3Ω V _{GS} =10V,R _{GEN} =3Ω	-	2.4	-	nS
Turn-on Rise Time	t _r		-	2.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	9	-	nS
Turn-Off Fall Time	t _f		-	2.5	-	nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =5A, V _{GS} =10V	-	12	-	nC
Gate-Source Charge	Q _{gs}		-	1.7	-	nC
Gate-Drain Charge	Q _{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =8A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

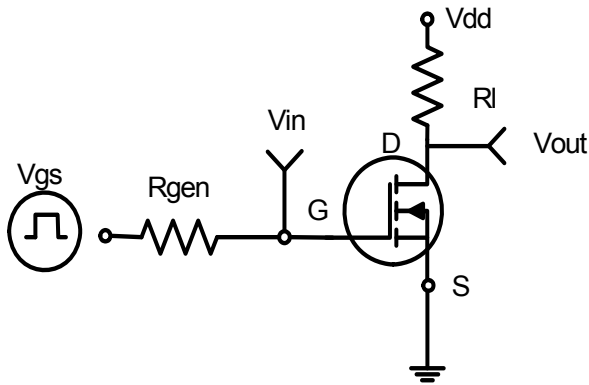


Figure 1: Switching Test Circuit

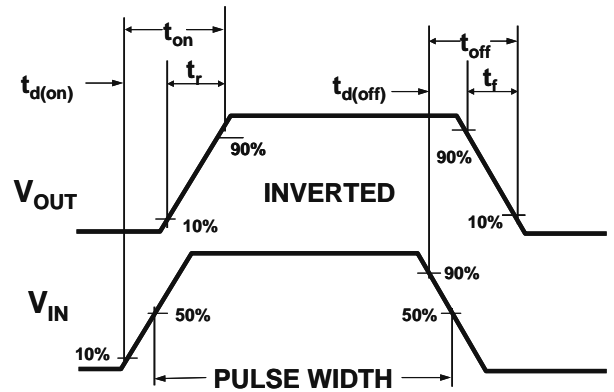


Figure 2: Switching Waveforms

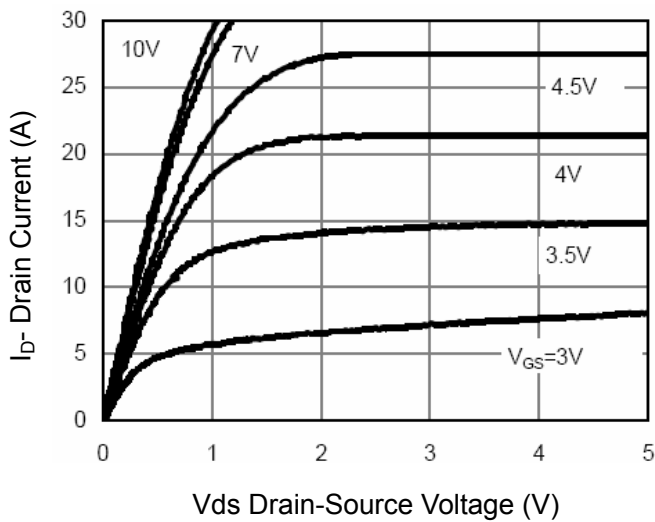


Figure 3 Output Characteristics

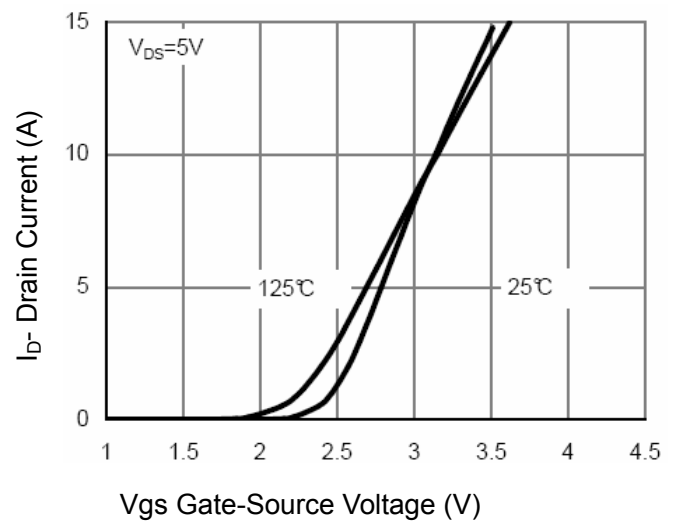


Figure 4 Transfer Characteristics

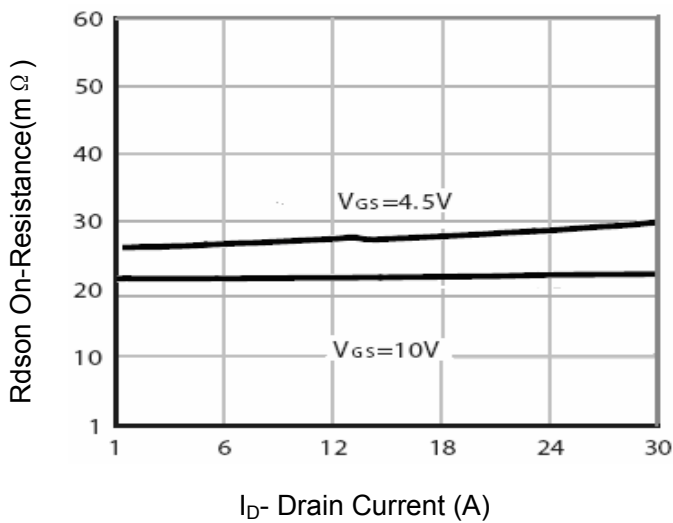


Figure 5 Drain-Source On-Resistance

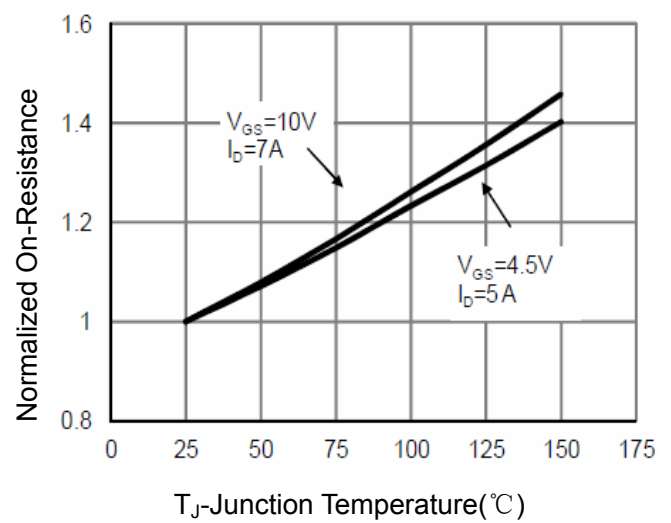
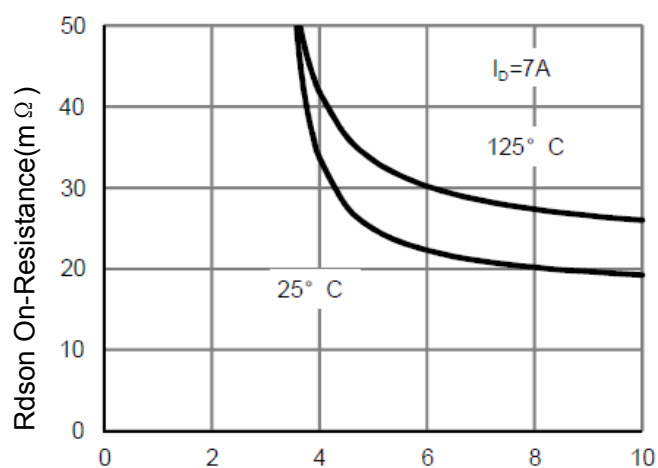
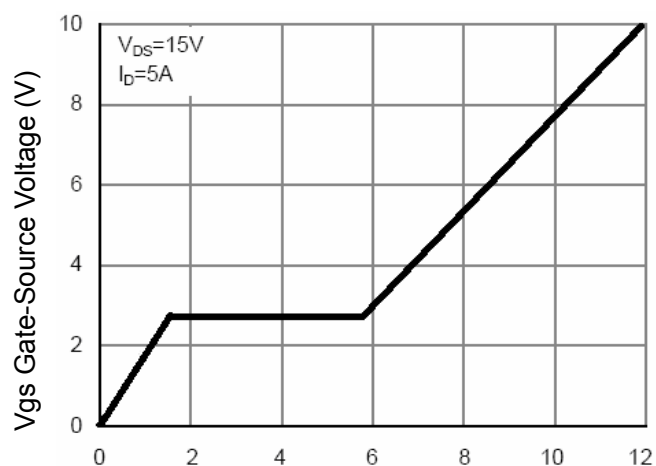


Figure 6 Drain-Source On-Resistance



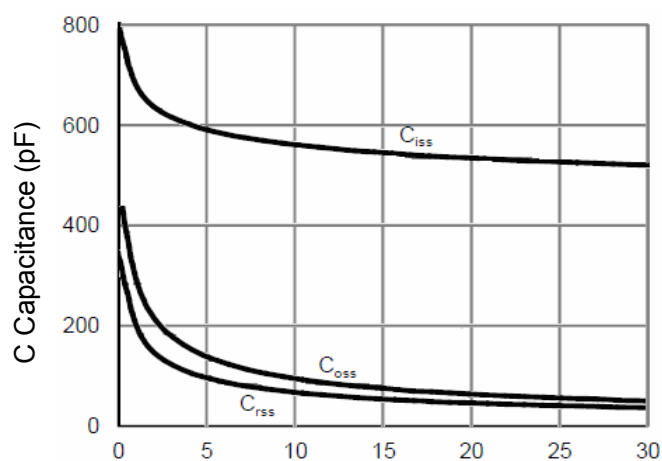
Vgs Gate-Source Voltage (V)

Figure7 Rdson vs Vgs



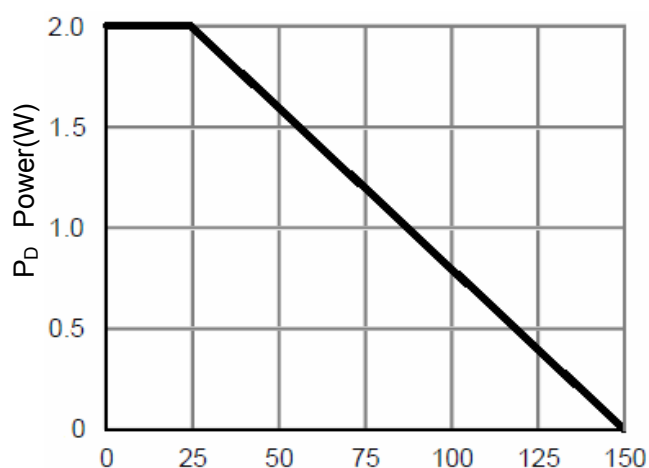
Qg Gate Charge (nC)

Figure 9 Gate Charge



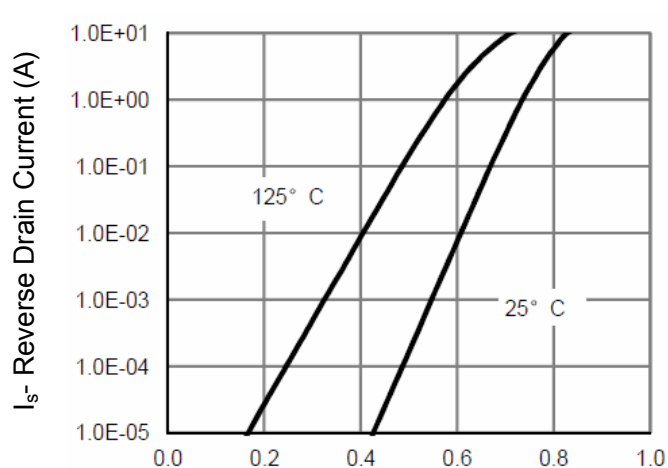
Vds Drain-Source Voltage (V)

Figure 11 Capacitance vs Vds



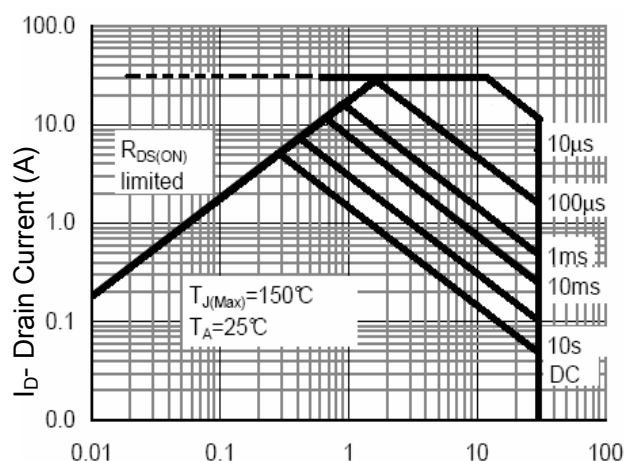
Tj-Junction Temperature(°C)

Figure 8 Power Dissipation



Vds Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area

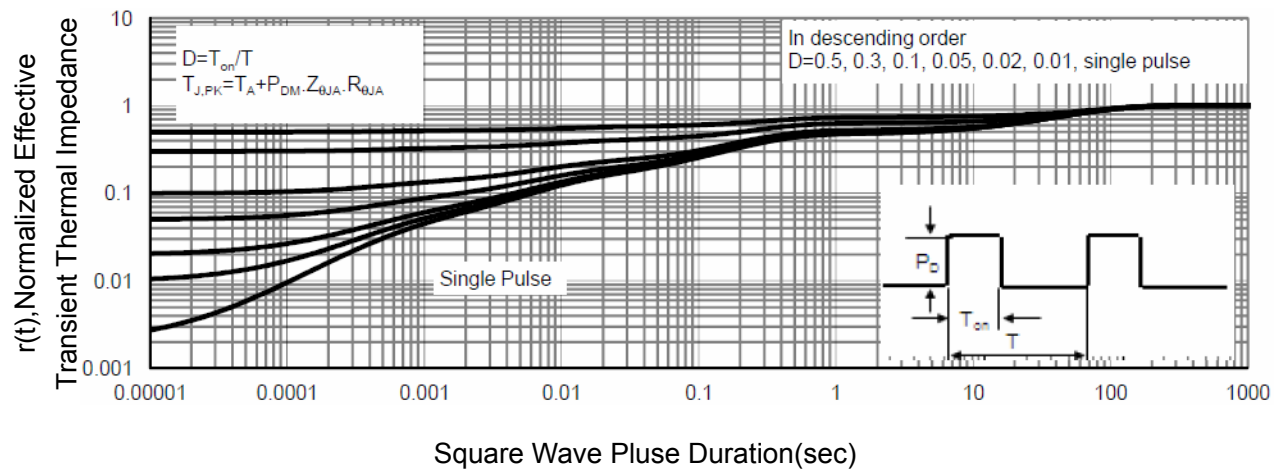
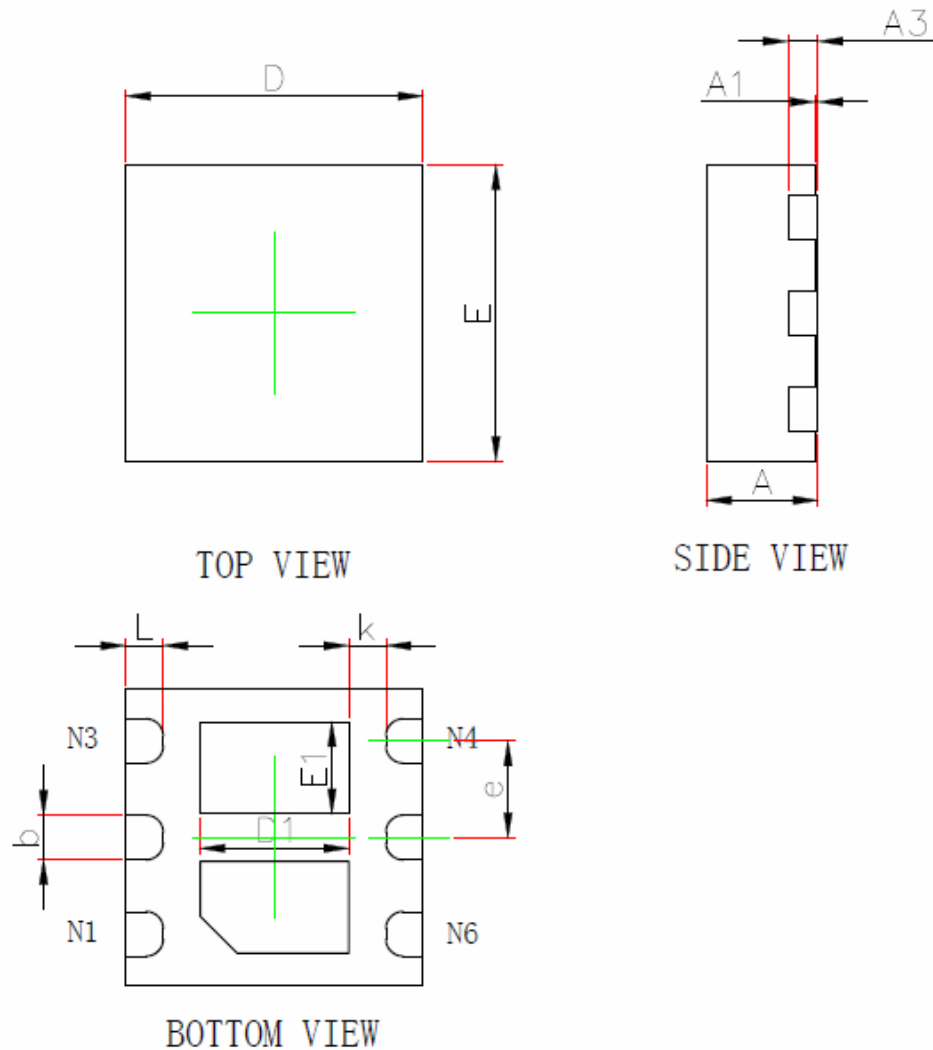


Figure 13 Normalized Maximum Transient Thermal Impedance

DFNWB2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.900	1.100	0.035	0.043
E1	0.520	0.720	0.020	0.028
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
k	0.200MIN.		0.008MIN.	
L	0.200	0.300	0.008	0.012